



# FGB40N60SM

## 600V, 40A Field Stop IGBT

### Features

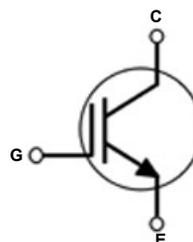
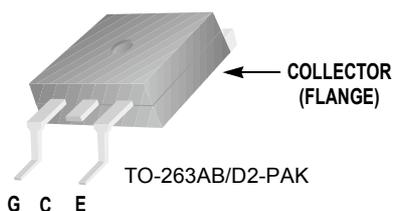
- Maximum Junction Temperature :  $T_J = 175^{\circ}\text{C}$
- Positive Temperature Co-efficient for easy parallel operating
- High current capability
- Low saturation voltage:  $V_{CE(sat)} = 1.9\text{V(Typ.) @ } I_C = 40\text{A}$
- High input impedance
- Fast switching
- Tighten Parameter Distribution
- RoHS compliant
- IR Reflow Only

### General Description

Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop 2nd generation IGBTs offer the optimum performance for welding and PFC applications where low conduction and switching losses are essential.

### Applications

- Welding, PFC



### Absolute Maximum Ratings

Symbol	Description	Ratings	Units
$V_{CES}$	Collector to Emitter Voltage	600	V
$V_{GES}$	Gate to Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^{\circ}\text{C}$	80	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	40	A
$I_{CM}$ (1)	Pulsed Collector Current	120	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^{\circ}\text{C}$	349	W
	Maximum Power Dissipation @ $T_C = 100^{\circ}\text{C}$	174	W
$T_J$	Operating Junction Temperature	-55 to +175	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
$T_L$	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^{\circ}\text{C}$

**Notes:**

1: Repetitive rating: Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.43	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	62.5	$^{\circ}\text{C}/\text{W}$

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGB40N60SM	FGB40N60SM	TO-263AB/D2-PAK	-	-	50

### Electrical Characteristics of the IGBT $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 250\mu\text{A}$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 250\mu\text{A}$	-	0.6	-	$\text{V}/^{\circ}\text{C}$
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{V}$	-	-	250	$\mu\text{A}$
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{V}$	-	-	$\pm 400$	nA
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	3.5	4.5	6.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40\text{A}, V_{GE} = 15\text{V}$	-	1.9	2.3	V
		$I_C = 40\text{A}, V_{GE} = 15\text{V}, T_C = 175^{\circ}\text{C}$	-	2.1	-	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	1880	-	pF
$C_{oes}$	Output Capacitance		-	180	-	pF
$C_{res}$	Reverse Transfer Capacitance		-	50	-	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{V}, I_C = 40\text{A}, R_G = 6\Omega, V_{GE} = 15\text{V}, \text{Inductive Load}, T_C = 25^{\circ}\text{C}$	-	12	16	ns
$t_r$	Rise Time		-	20	28	ns
$t_{d(off)}$	Turn-Off Delay Time		-	92	120	ns
$t_f$	Fall Time		-	13	17	ns
$E_{on}$	Turn-On Switching Loss		-	0.87	1.30	mJ
$E_{off}$	Turn-Off Switching Loss		-	0.26	0.34	mJ
$E_{ts}$	Total Switching Loss		-	1.13	1.64	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{V}, I_C = 40\text{A}, R_G = 6\Omega, V_{GE} = 15\text{V}, \text{Inductive Load}, T_C = 175^{\circ}\text{C}$	-	15	-	ns
$t_r$	Rise Time		-	22	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	116	-	ns
$t_f$	Fall Time		-	16	-	ns
$E_{on}$	Turn-On Switching Loss		-	0.97	-	mJ
$E_{off}$	Turn-Off Switching Loss		-	0.60	-	mJ
$E_{ts}$	Total Switching Loss		-	1.57	-	mJ

**Electrical Characteristics of the IGBT** (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Units
$Q_g$	Total Gate Charge	$V_{CE} = 400V, I_C = 40A,$ $V_{GE} = 15V$	-	119	180	nC
$Q_{ge}$	Gate to Emitter Charge		-	13	20	nC
$Q_{gc}$	Gate to Collector Charge		-	58	90	nC

## Typical Performance Characteristics

Figure 1. Typical Output Characteristics

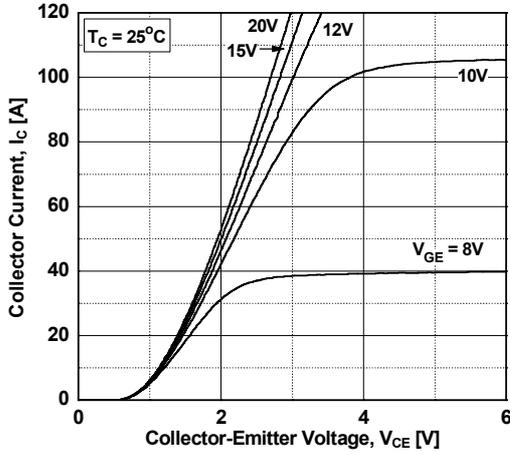


Figure 2. Typical Output Characteristics

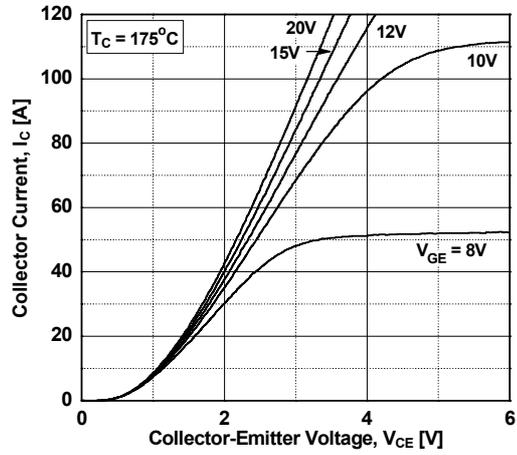


Figure 3. Typical Saturation Voltage Characteristics

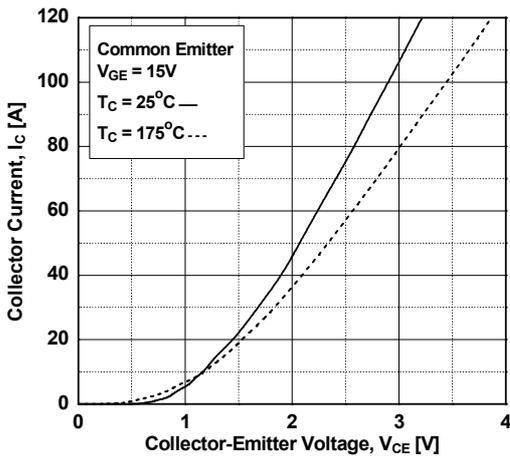


Figure 4. Transfer Characteristics

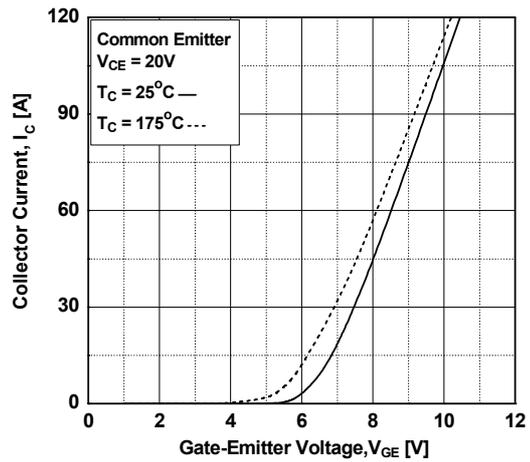


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

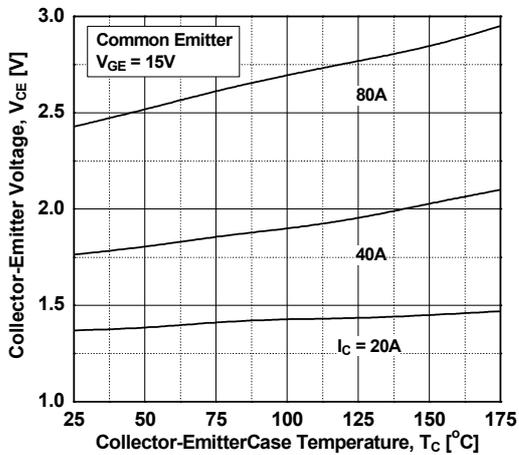
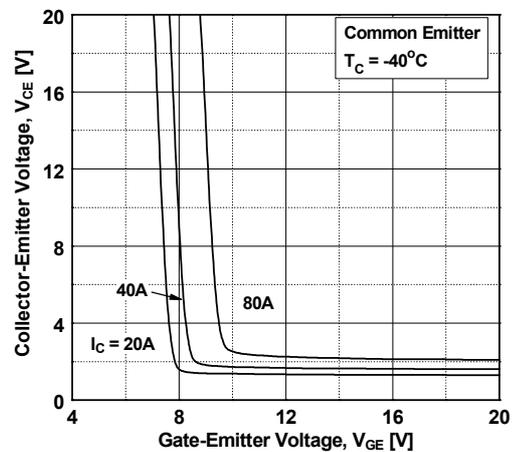


Figure 6. Saturation Voltage vs. Vge



## Typical Performance Characteristics

Figure 7. Saturation Voltage vs.  $V_{GE}$

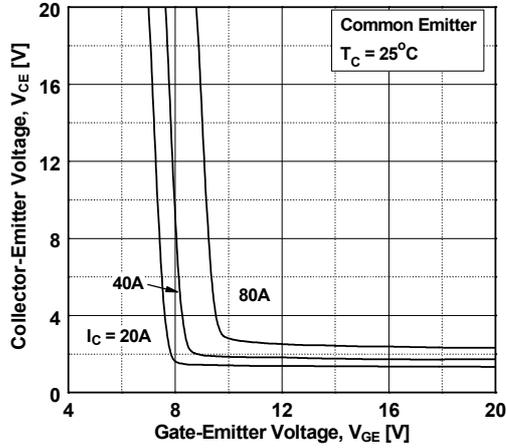


Figure 8. Saturation Voltage vs.  $V_{GE}$

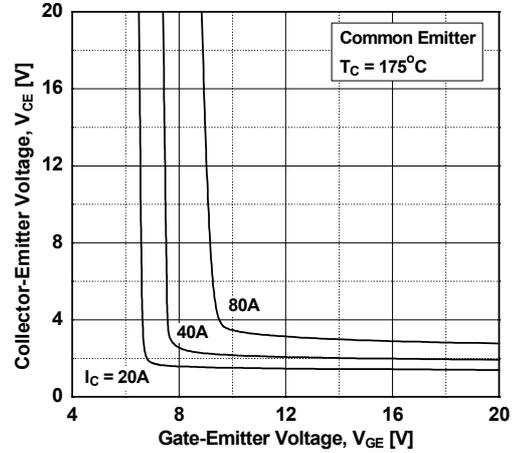


Figure 9. Capacitance Characteristics

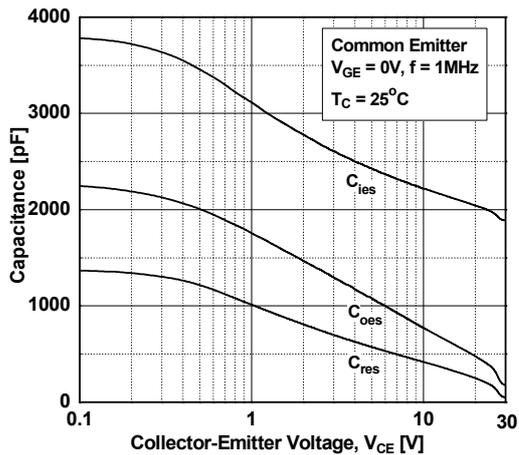


Figure 10. Gate charge Characteristics

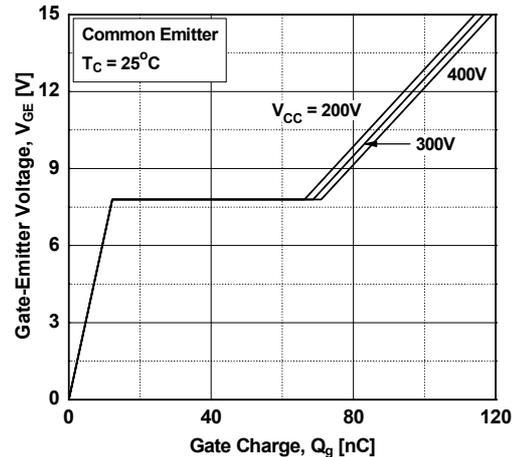


Figure 11. SOA Characteristics

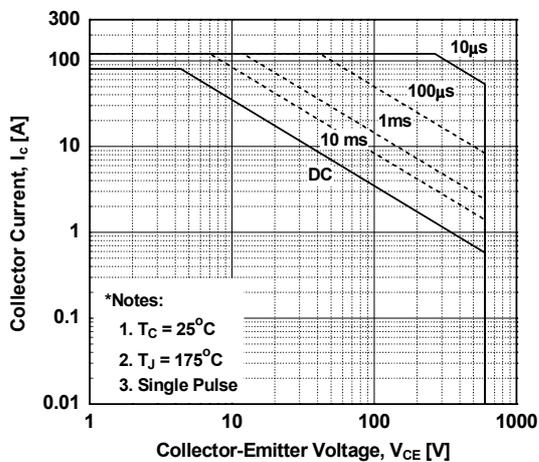
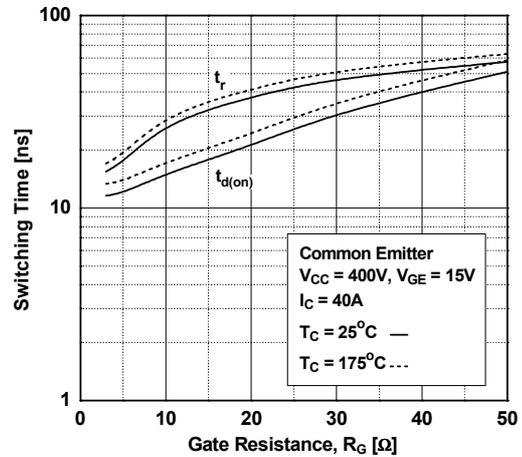
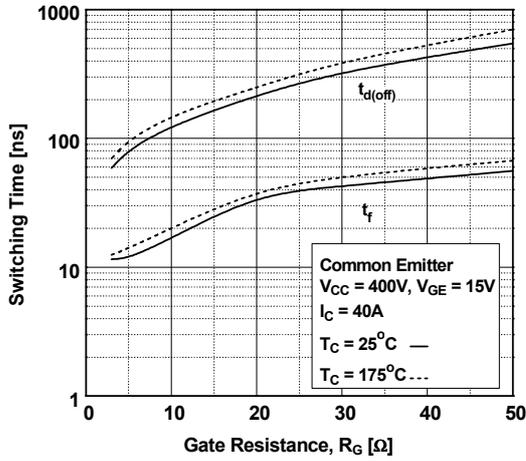


Figure 12. Turn-on Characteristics vs. Gate Resistance

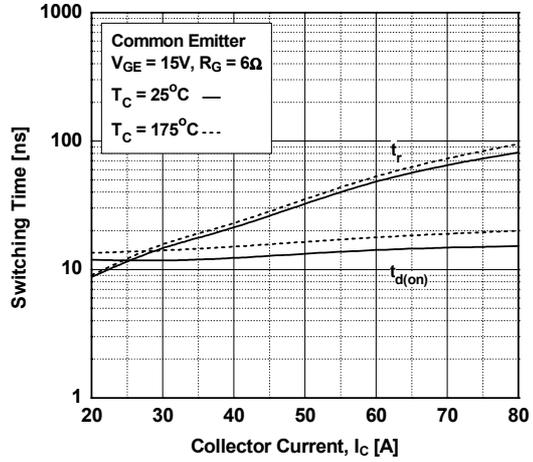


## Typical Performance Characteristics

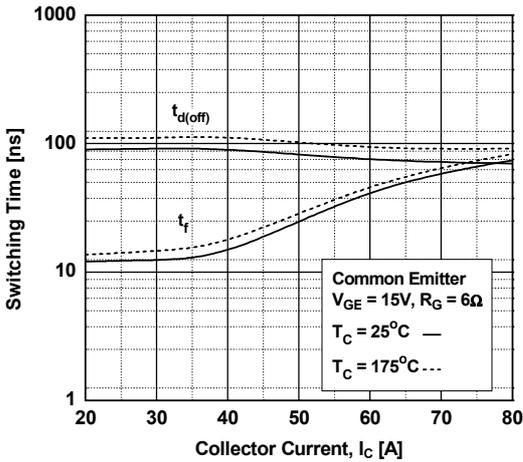
**Figure 13. Turn-off Characteristics vs. Gate Resistance**



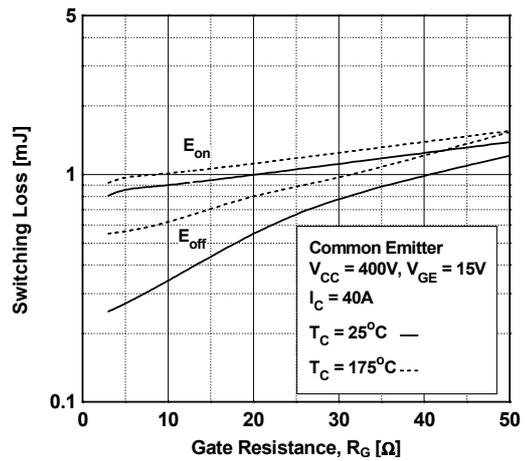
**Figure 14. Turn-on Characteristics vs. Collector Current**



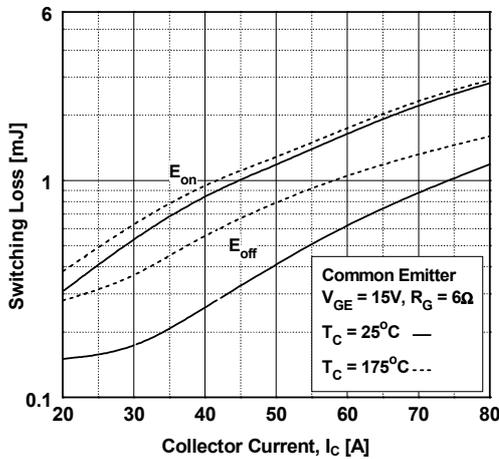
**Figure 15. Turn-off Characteristics vs. Collector Current**



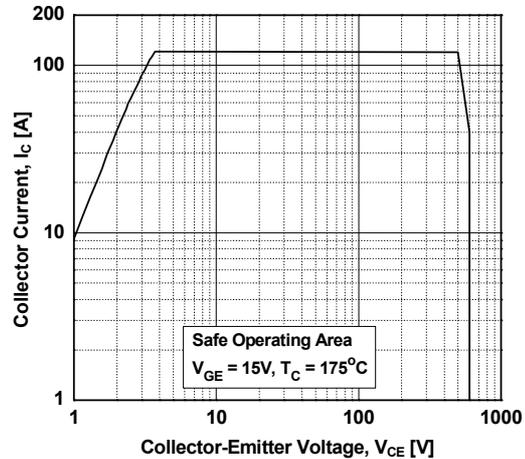
**Figure 16. Switching Loss vs. Gate Resistance**



**Figure 17. Switching Loss vs. Collector Current**



**Figure 18. Turn off Switching SOA Characteristics**



## Typical Performance Characteristics

Figure 19. Current Derating

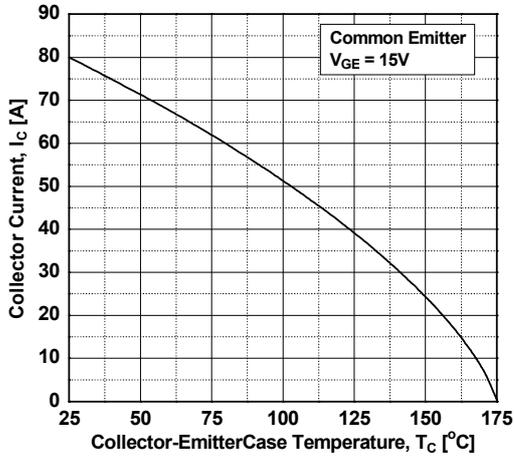


Figure 20. Load Current Vs. Frequency

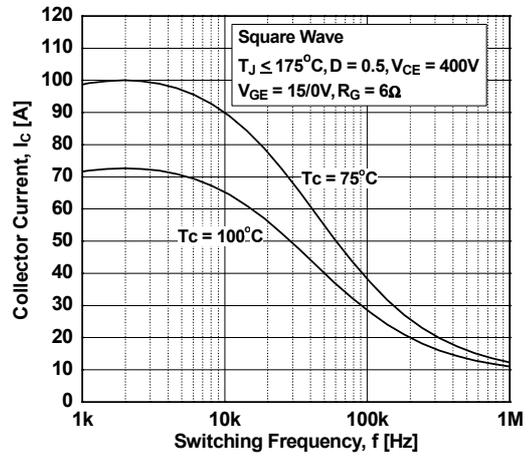
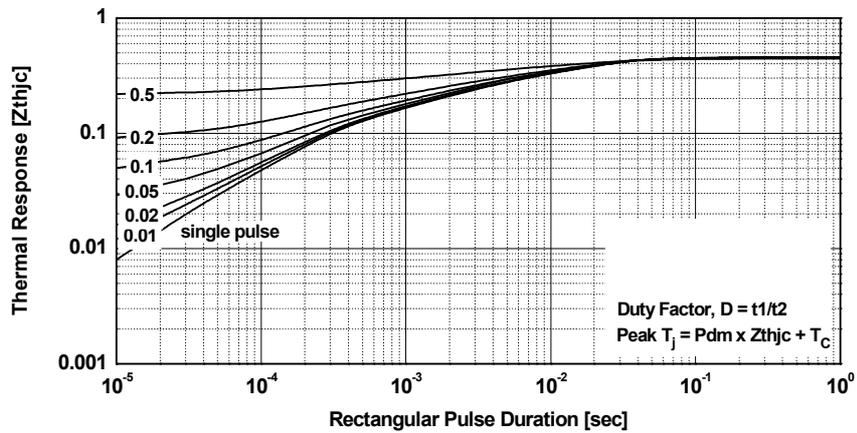
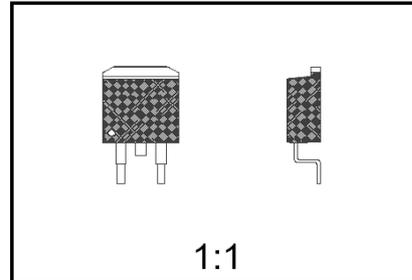
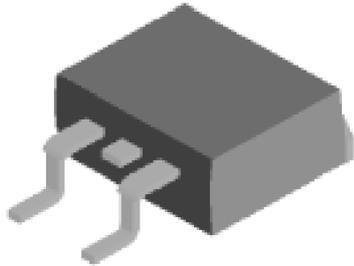


Figure 21. Transient Thermal Impedance of IGBT



## Mechanical Dimensions

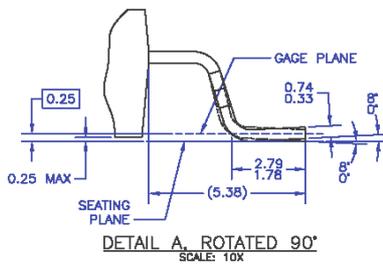
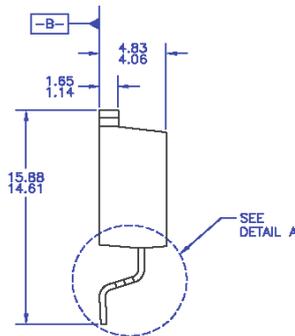
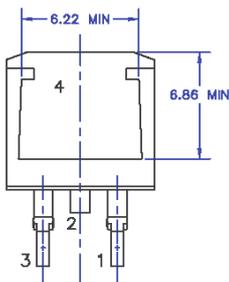
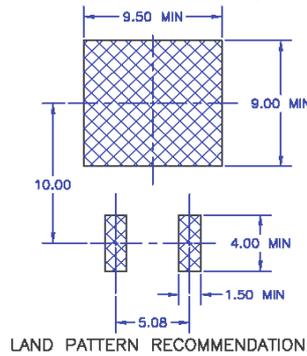
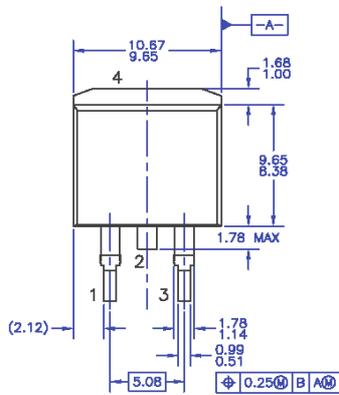
# TO-263AB/D<sup>2</sup>-PAK



Scale 1:1 on letter size paper

Dimensions shown below are in:  
millimeters

Part Weight per unit (gram): 1.4378



- NOTES: UNLESS OTHERWISE SPECIFIED
- ALL DIMENSIONS ARE IN MILLIMETERS.
  - REFERENCE JEDEC, TO-263, ISSUE D, VARIATION AB, DATED JULY 2003.
  - DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1982.
  - LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
  - PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

TO263A02REVD



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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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